



01N45

Preliminary

Power MOSFET

0.1A, 450V N-CHANNEL POWER MOSFET

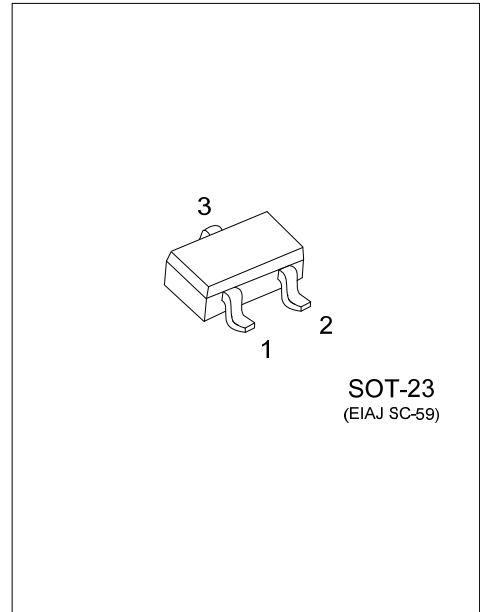
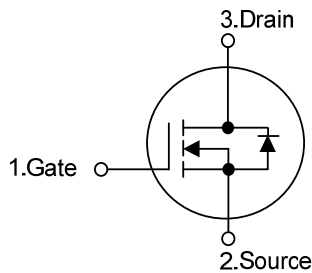
DESCRIPTION

The UTC **01N45** is a N-channel mode power MOSFET using UTC's advanced technology to provide customers with a minimum on-state resistance, low gate charge and superior switching performance.

FEATURES

- * $R_{DS(ON)} \leq 16\Omega @ V_{GS}=10V, I_D=0.05A$
- * High switching speed
- * Typically 5.76nC low gate charge
- * 100% avalanche tested

SYMBOL



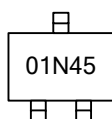
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
01N45L-AE3-R	01N45G-AE3-R	SOT-23	G	S	D	Tape Reel

Note: Pin Assignment: G: Gate S: Source D: Drain

01N45G-AE3-R	(1)Packing Type	(1) R: Tape Reel
	(2)Package Type	(2) AE3: SOT-23
	(3)Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free

MARKING



■ ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	450	V
Gate-Source Voltage	V_{GSS}	± 30	V
Continuous Drain Current	I_D	0.1	A
Avalanche Current	I_{AR}	0.1	A
Power Dissipation	P_D	0.3	W
Junction Temperature	T_J	+150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

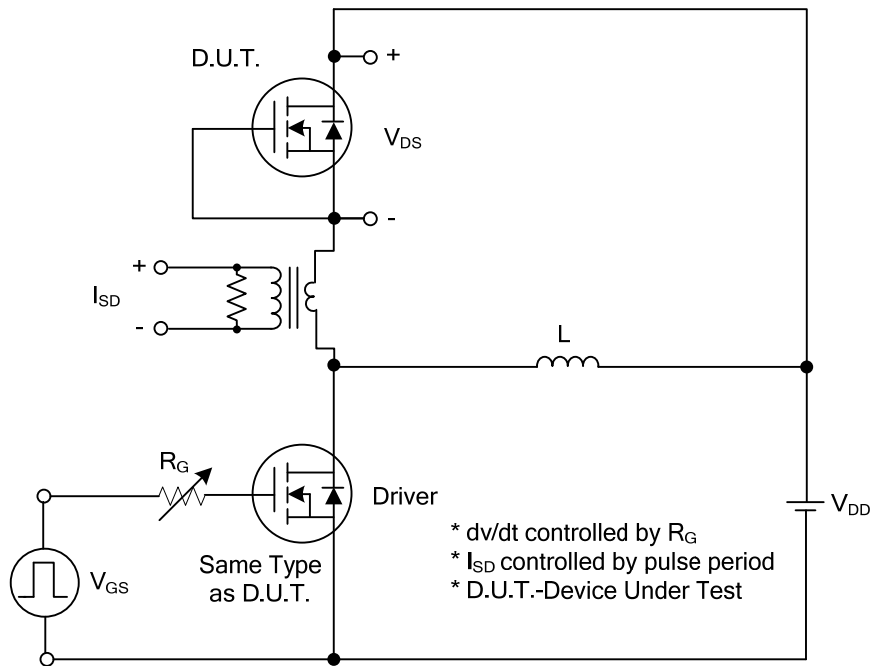
Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature

■ ELECTRICAL CHARACTERISTICS

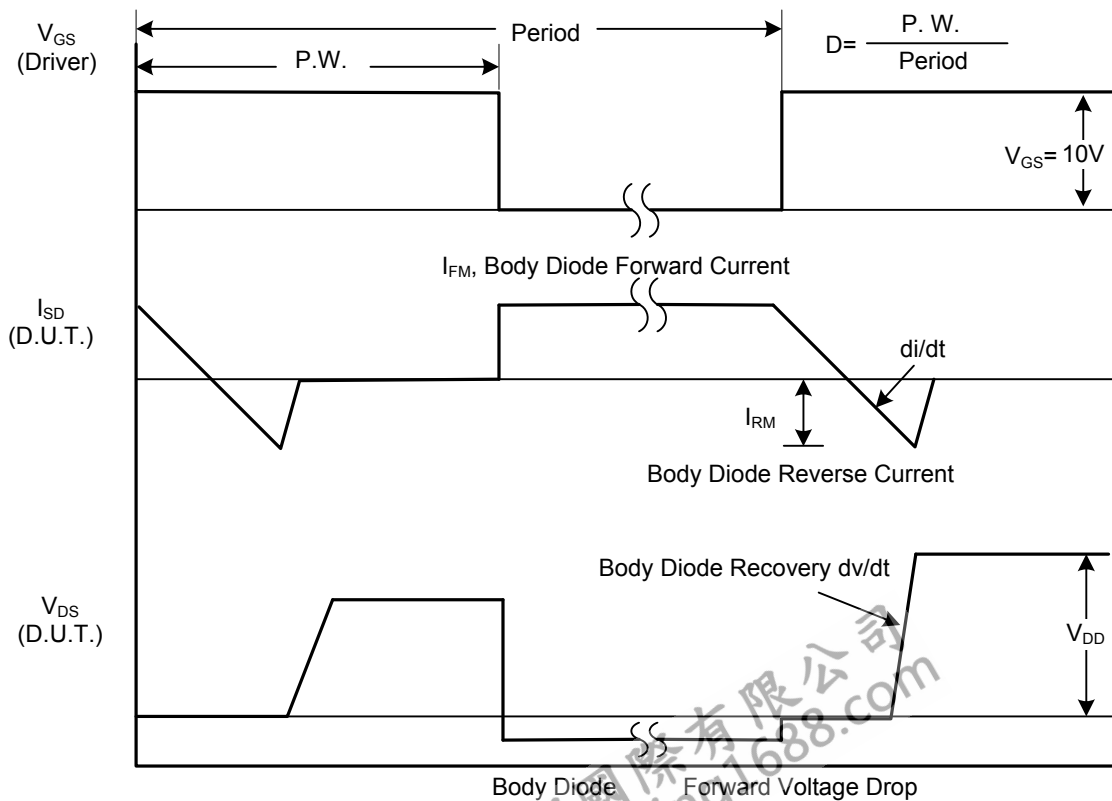
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}, V_{DS}=0\text{V}$	450			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=450\text{V}$			10	μA
Gate-Source Leakage Current	I_{GSS}	Forward			+100	nA
		Reverse			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$I_D=250\mu\text{A}$	1.0		3.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=0.05\text{A}$			16	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}, V_{DS}=25\text{V}, f=1\text{MHz}$		133		pF
Output Capacitance	C_{OSS}			13		pF
Reverse Transfer Capacitance	C_{RSS}			5		pF
SWITCHING PARAMETERS						
Total Gate Charge	Q_G	$V_{DS}=50\text{V}, V_{GS}=10\text{V}, I_D=0.5\text{A}$ $I_G=100\mu\text{A}$ (Note1, 2)		5.76		nC
Gate to Source Charge	Q_{GS}			0.26		nC
Gate to Drain Charge	Q_{GD}			0.54		nC
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DS}=30\text{V}, V_{GS}=10\text{V}, I_D=0.5\text{A},$ $R_G=25\Omega$ (Note1, 2)		14.4		ns
Rise Time	t_R			16.8		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			62.8		ns
Fall-Time	t_F			46		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V_{SD}	$I_S=0.1\text{A}, V_{GS}=0\text{V}$			1.4	V
Maximum Body-Diode Continuous Current	I_S				0.1	A
Maximum Body-Diode Pulsed Current	I_{SM}				0.4	A
Reverse Recovery Time	t_{rr}	$V_{GS}=0\text{V}, I_S=0.1\text{A},$		43.6		ns
Reverse Recovery Charge	Q_{rr}	$dI_F/dt=100\text{A}/\mu\text{s}$		49		nC

Notes: 1. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

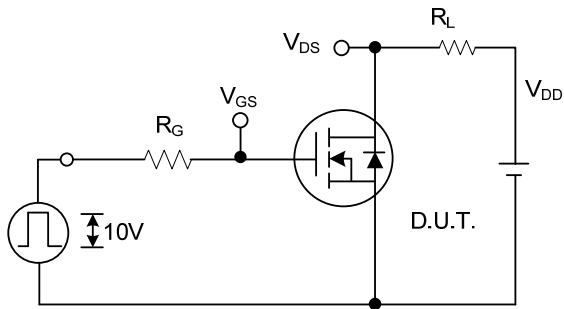


Peak Diode Recovery dv/dt Test Circuit

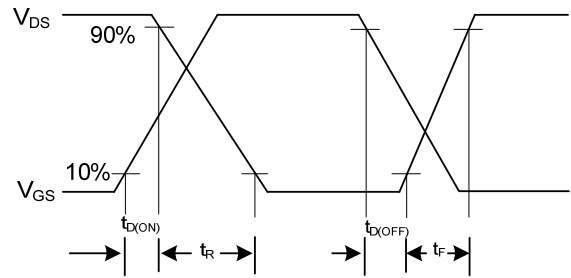


Peak Diode Recovery dv/dt Waveforms

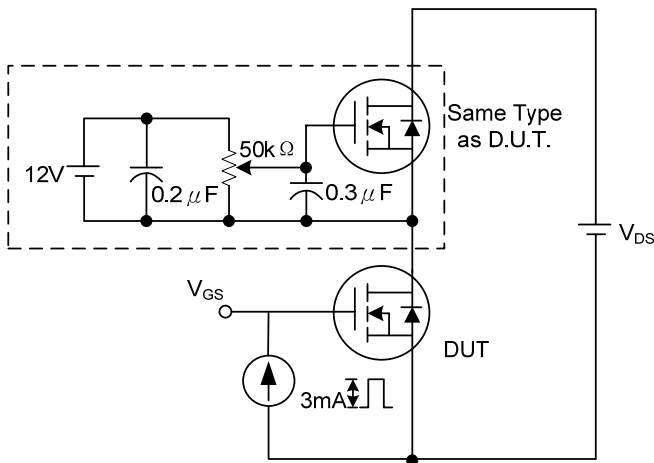
■ TEST CIRCUITS AND WAVEFORMS



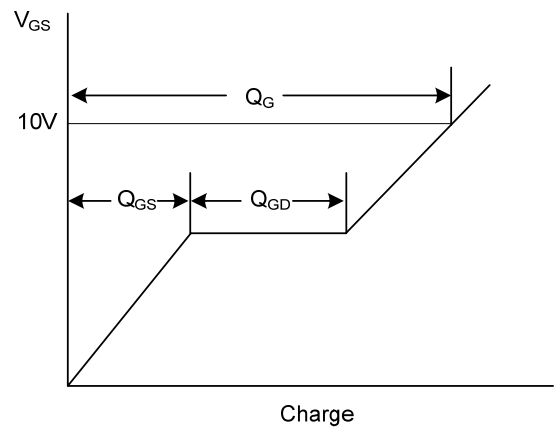
Switching Test Circuit



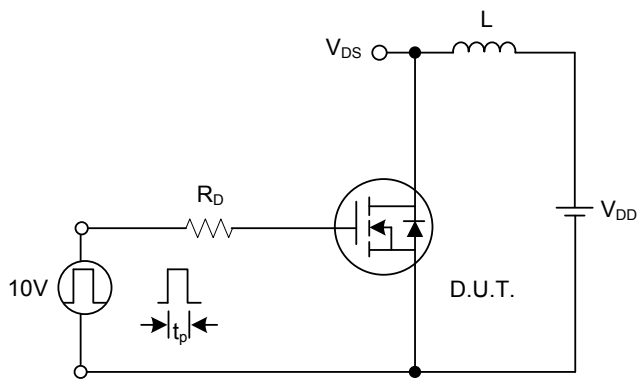
Switching Waveforms



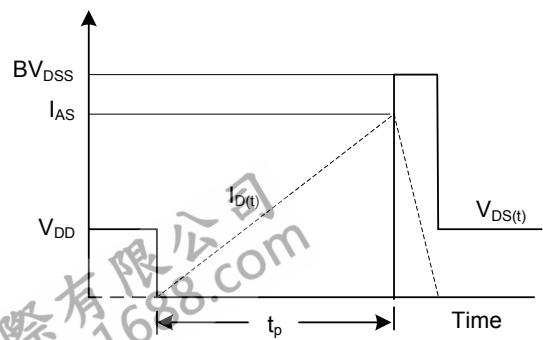
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.